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(54) Title: HIGH ELECTRON MOBILITY TRANSISTOR AND METHOD OF MANUFACTURING THEREOF

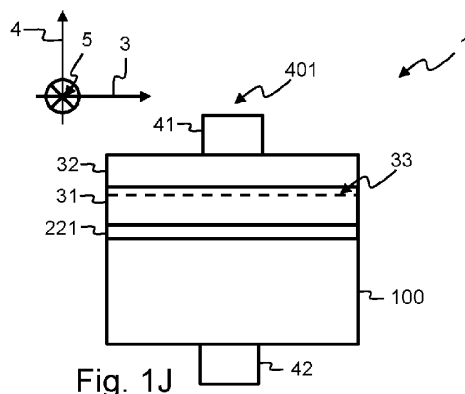


Fig. 1J

(57) Abstract: A method of manufacturing a high electron mobility transistor (1), said method comprising the steps of: - providing a target wafer (10) comprising a target substrate (100); - providing a donor wafer (20) comprising an epitaxial donor film (21); - bonding said donor film (21) to said target wafer (10); - separating said donor wafer (20) and said target wafer (10) along said first donor III-N layer (201), thereby forming on said target wafer (10) a top surface layer (221) of 200nm or less; - epitaxially growing an epitaxial III-N semiconductor layer stack (31, 32) on top of said top surface layer (221); - forming a gate contact (41) in a gate region (401); and - forming a substrate galvanic contact (42) contacting said target substrate (100).

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